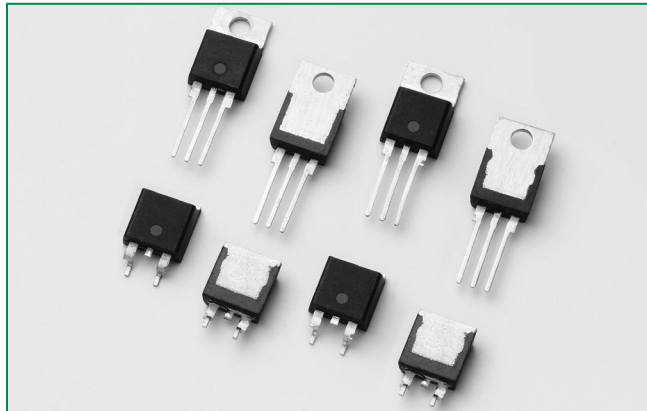


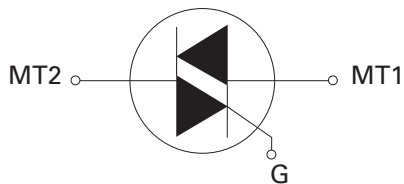
**QJxx16xHx Series**



**Main Features**

Symbol	Value	Unit
$I_{T(RMS)}$	16	A
$V_{DRM}/V_{RRM}$	400 or 600	V
$I_{GT (Q1)}$	10 to 80	mA

**Schematic Symbol**



**Description**

This 16A high temperature alternistor triac solid state switch series is designed for AC switching and phase control applications such as motor speed and temperature modulation controls, lighting controls, and static switching relays.

Alternistor type components only operate in quadrants I, II, & III and are used in circuits requiring high dv/dt capability.

**Features & Benefits**

- Voltage capability up to 600V
- Surge capability up to 200A at 60Hz half cycle
- Solid-state switching eliminates arcing or contact bounce that create voltage transients
- No contacts to wear out from reaction of switching events
- Restricted (or limited) RFI generation, depending on activation point in sine wave
- Requires only a short gate activation pulse in each half-cycle
- Halogen free and RoHS compliant

**Applications**

Excellent for AC switching and phase control applications such as heating, lighting, and motor speed controls.

Typical applications are AC solid-state switches, light dimmers, power tools, lawn care equipment, home/brown goods and white goods appliances.

Alternistor Triacs (no snubber required) are used in applications with high inductive loads requiring the highest commutation performance.

Internally constructed isolated packages are offered for ease of heat sinking with highest isolation voltage.

### Absolute Maximum Ratings — Alternistor Triac (3 Quadrants)

Symbol	Parameter	Value	Unit	
$I_{T(RMS)}$	RMS on-state current (full sine wave)	QJxx16LHy $T_C = 115^\circ\text{C}$	16	A
		QJxx16RHyy QJxx16NHyy $T_C = 130^\circ\text{C}$		
$I_{TSM}$	Non repetitive surge peak on-state current (Single half cycle, $T_J$ initial = $25^\circ\text{C}$ )	f = 50Hz t = 20 ms	167	A
		f = 60Hz t = 16.7 ms		
$I^2t$	$I^2t$ Value for fusing	$t_p = 8.3$ ms	166	$\text{A}^2\text{s}$
di/dt	Critical rate of rise of on-state current	f = 60Hz $T_J = 125^\circ\text{C}$	100	$\text{A}/\mu\text{s}$
$I_{GTM}$	Peak gate trigger current	$t_p \leq 10\mu\text{s};$ $I_{GT} \leq I_{GTM}$ $T_J = 125^\circ\text{C}$	2.0	A
$P_{G(AV)}$	Average gate power dissipation	$T_J = 125^\circ\text{C}$	0.5	W
$T_{stg}$	Storage temperature range		-40 to 150	$^\circ\text{C}$
$T_J$	Operating junction temperature range		-40 to 150	$^\circ\text{C}$
$V_{DSM}/V_{RSM}$	Peak non-repetitive blocking voltage	Pw=100 $\mu\text{s}$	$V_{DRM}/V_{RRM}+100$	V

xx = voltage/10, y = sensitivity

### Electrical Characteristics ( $T_J = 25^\circ\text{C}$ , unless otherwise specified) — Alternistor Triac (3 Quadrants)

Symbol	Test Conditions	Quadrant	QJxx16xH2	QJx16xH3	QJx16xH4	QJx16xH6	Unit	
$I_{GT}$	$V_D = 12\text{V}$ $R_L = 60\Omega$	I – II – III	MAX.	10	20	35	80	mA
$V_{GT}$		I – II – III	MAX.	1.3				V
$V_{GD}$	$V_D = V_{DRM}$ $R_L = 3.3\text{k}\Omega$ $T_J = 150^\circ\text{C}$	I – II – III	MIN.	0.15				V
$I_H$	$I_T = 100\text{mA}$		MAX.	15	35	50	70	mA
dv/dt	$V_D = V_{DRM}$ Gate Open $T_J = 150^\circ\text{C}$	600V	MIN.	-	250	350	850	$\text{V}/\mu\text{s}$
	$V_D = 2/3 V_{DRM}$ Gate Open $T_J = 150^\circ\text{C}$	600V	MIN.	50	300	400	925	
(dv/dt)c	(di/dt)c = 8.6 A/ms $T_J = 150^\circ\text{C}$		MIN.	2	20	25	30	$\text{V}/\mu\text{s}$
$t_{gt}$	$I_G = 2 \times I_{GT}$ PW = 15 $\mu\text{s}$ $I_T = 22.6$ A(pk)		TYP.	3	3	3	5	$\mu\text{s}$

### Static Characteristics

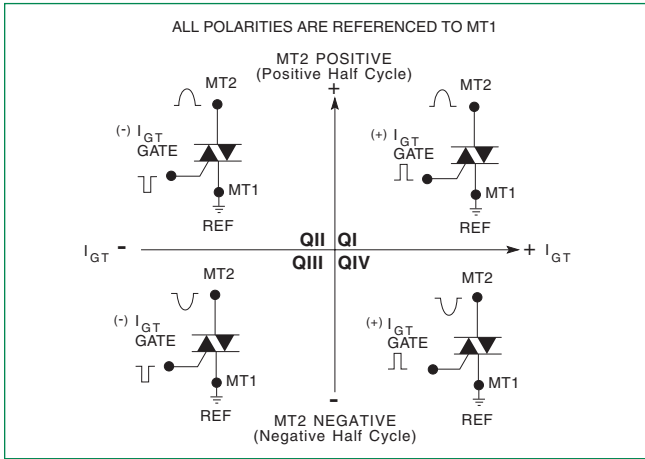
Symbol	Test Conditions	Value	Unit		
$V_{TM}$	$I_T = 22.6\text{A}$ $t_p = 380\mu\text{s}$	MAX	1.60	V	
$I_{DRM}/I_{RRM}$	@ $V_{DRM}/V_{RRM}$	$T_J = 25^\circ\text{C}$	MAX	5	$\mu\text{A}$
		$T_J = 150^\circ\text{C}$		4	mA

### Thermal Resistances

Symbol	Parameter	Value	Unit	
$R_{\theta(J-C)}$	Junction to case (AC)	QJxx16RHyy QJxx16NHyy	0.90	$^\circ\text{C}/\text{W}$
		QJxx16LHy	1.8	
$R_{\theta(J-A)}$	Junction to ambient	QJxx16RHyy QJxx16NHyy	45	$^\circ\text{C}/\text{W}$
		QJxx16LHy	50	

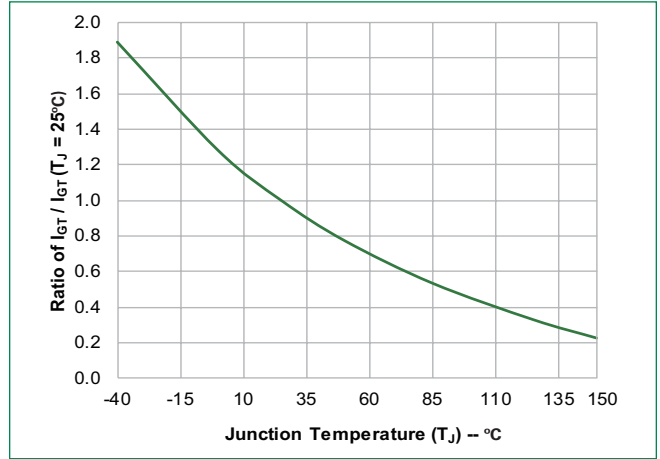
xx = voltage/10; y = sensitivity

**Figure 1: Definition of Quadrants**

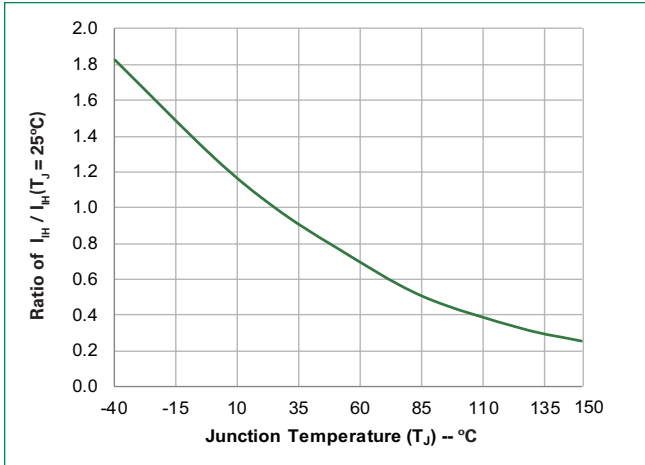


Note: Alternistors will not operate in QIV

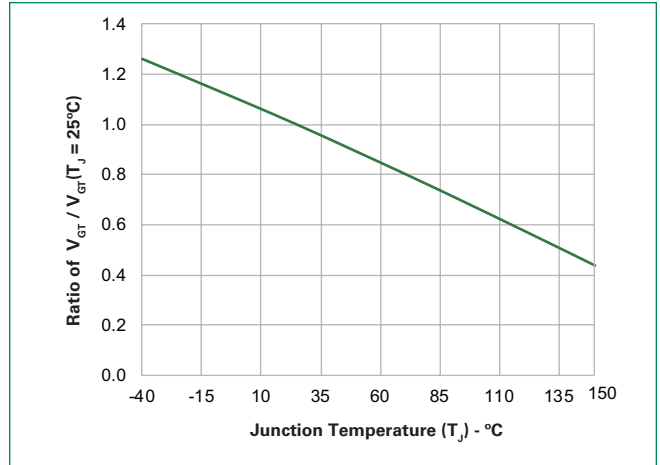
**Figure 2: Normalized DC Gate Trigger Current for All Quadrants vs. Junction Temperature**



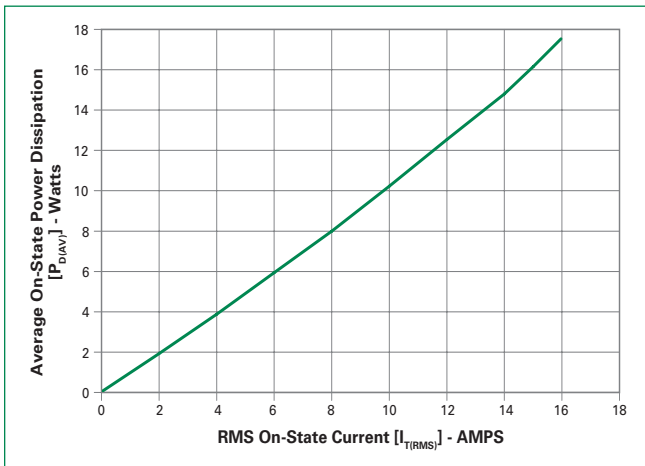
**Figure 3: Normalized DC Holding Current vs. Junction Temperature**



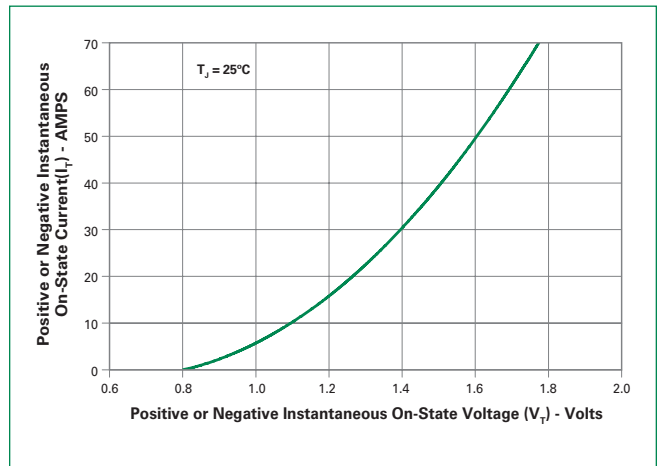
**Figure 4: Normalized DC Gate Trigger Voltage for All Quadrants vs. Junction Temperature**



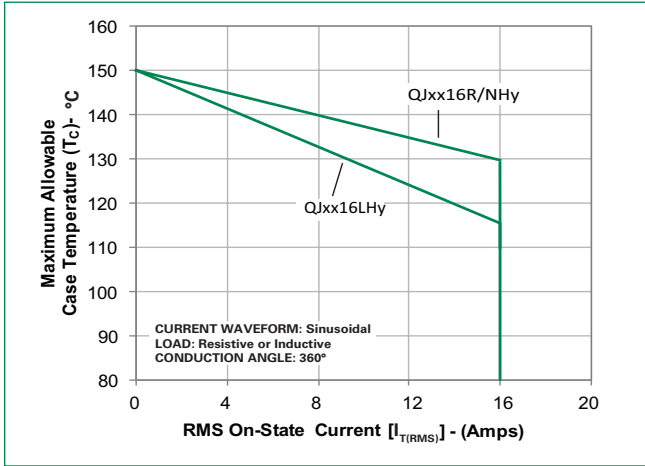
**Figure 5: Power Dissipation (Typical) vs. RMS On-State Current**



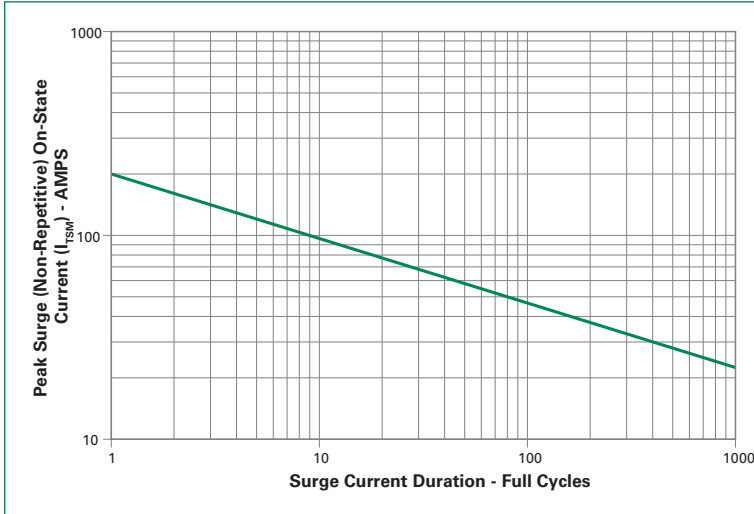
**Figure 6: On-State Current vs. On-State Voltage (Typical)**



**Figure 6: Maximum Allowable Case Temperature vs. RMS On-State Current**



**Figure 9: Surge Peak On-State Current vs. Number of Cycles**

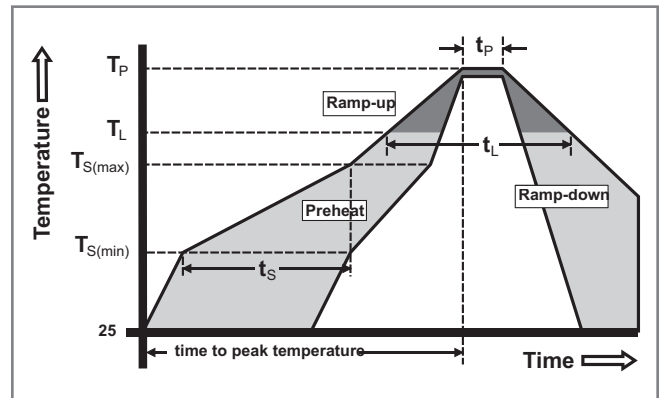


Supply Frequency: 60Hz Sinusoidal  
Load: Resistive  
RMS On-State [IT(RMS)]: Max Rated Value at Specific Case Temperature

- Notes:
1. Gate control may be lost during and immediately following surge current interval.
  2. Overload may not be repeated until junction temperature has returned to steady-state rated value.

**Soldering Parameters**

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ( $T_{s(min)}$ )	150°C
	- Temperature Max ( $T_{s(max)}$ )	200°C
	- Time (min to max) ( $t_s$ )	60 – 180 secs
Average ramp up rate (Liquidus Temp) ( $T_L$ ) to peak		5°C/second max
$T_{S(max)}$ to $T_L$ - Ramp-up Rate		5°C/second max
Reflow	- Temperature ( $T_L$ ) (Liquidus)	217°C
	- Time ( $t_r$ )	60 – 150 seconds
Peak Temperature ( $T_p$ )		260 <sup>+0/-5</sup> °C
Time within 5°C of actual peak Temperature ( $t_p$ )		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature ( $T_p$ )		8 minutes Max.
Do not exceed		280°C



### Physical Specifications

<b>Terminal Finish</b>	100% Matte Tin-plated
<b>Body Material</b>	UL Recognized epoxy meeting flammability rating V-0
<b>Terminal Material</b>	Copper Alloy

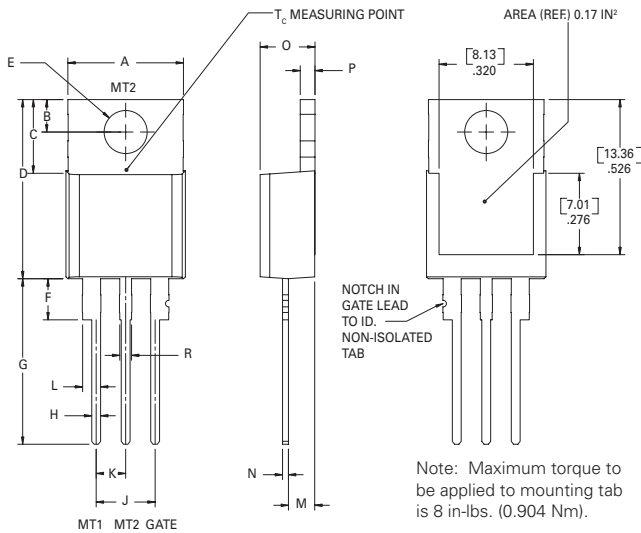
### Design Considerations

Careful selection of the correct component for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the component rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

### Environmental Specifications

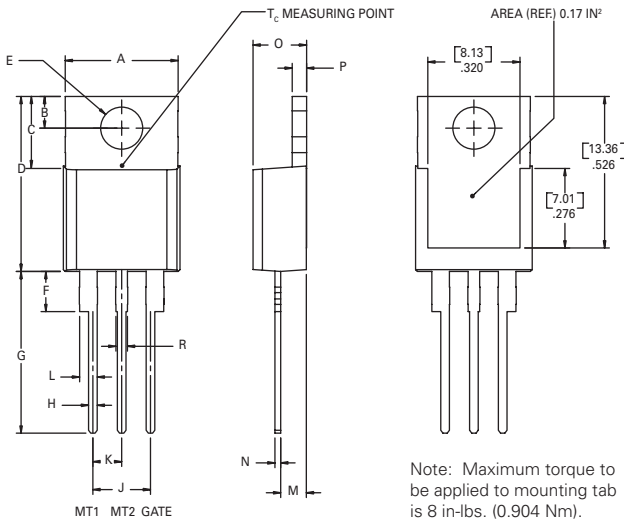
Test	Specifications and Conditions
<b>AC Blocking</b>	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 150°C for 1008 hours
<b>Temperature Cycling</b>	MIL-STD-750, M-1051, 100 cycles; -40°C to +150°C; 15-min dwell time
<b>Temperature/Humidity</b>	EIA / JEDEC, JESD22-A101 1008 hours; 160V - DC: 85°C; 85% rel humidity
<b>High Temp Storage</b>	MIL-STD-750, M-1031, 1008 hours; 150°C
<b>Low-Temp Storage</b>	1008 hours; -40°C
<b>Resistance to Solder Heat</b>	MIL-STD-750 Method 2031
<b>Solderability</b>	ANSI/J-STD-002, category 3, Test A
<b>Lead Bend</b>	MIL-STD-750, M-2036 Cond E
<b>Moisture Sensitivity Level</b>	Level 1, JEDEC-J-STD-020

### Dimensions — TO-220AB (R-Package) — Non-Isolated Mounting Tab Common with Center Lead



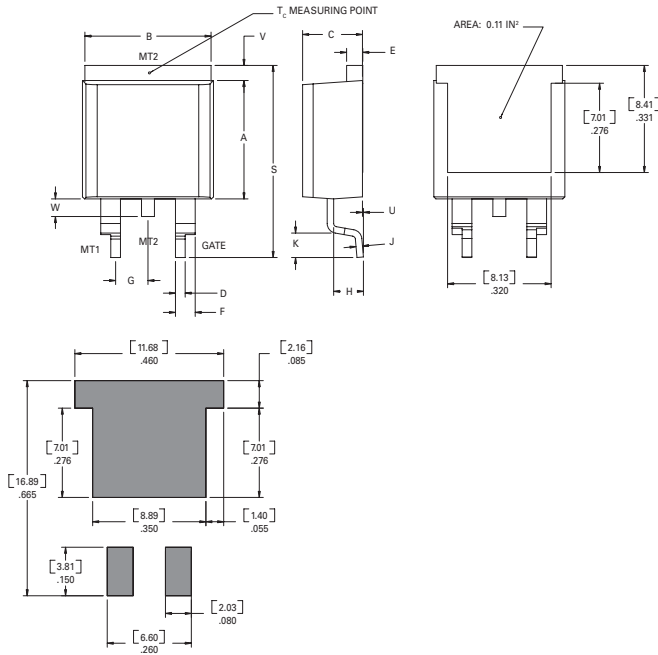
Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.66	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

### Dimensions — TO-220AB (L-Package) — Isolated Mounting Tab



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.60
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

### Dimensions — TO-263AB (N-Package) — D<sup>2</sup>Pak Surface Mount



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.360	0.370	9.14	9.40
B	0.380	0.420	9.65	10.67
C	0.178	0.188	4.52	4.78
D	0.025	0.035	0.64	0.89
E	0.045	0.060	1.14	1.52
F	0.060	0.075	1.52	1.91
G	0.095	0.105	2.41	2.67
H	0.092	0.102	2.34	2.59
J	0.018	0.024	0.46	0.61
K	0.090	0.110	2.29	2.79
S	0.590	0.625	14.99	15.88
V	0.035	0.045	0.89	1.14
U	0.002	0.010	0.05	0.25
W	0.040	0.070	1.02	1.78

### Product Selector

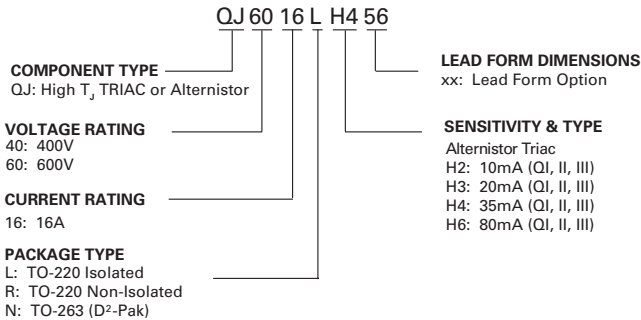
Part Number	Voltage		Gate Sensitivity Quadrants	Type	Package
	400V	600V	I – II – III		
QJxx16LH2	X	X	10 mA	Alternistor Triac	TO-220L
QJxx16RH2	X	X	10 mA	Alternistor Triac	TO-220R
QJxx16NH2	X	X	10 mA	Alternistor Triac	TO-263 D <sup>2</sup> -PAK
QJxx16LH3	X	X	20 mA	Alternistor Triac	TO-220L
QJxx16RH3	X	X	20 mA	Alternistor Triac	TO-220R
QJxx16NH3	X	X	20 mA	Alternistor Triac	TO-263 D <sup>2</sup> -PAK
QJxx16LH4	X	X	35 mA	Alternistor Triac	TO-220L
QJxx16RH4	X	X	35 mA	Alternistor Triac	TO-220R
QJxx16NH4	X	X	35 mA	Alternistor Triac	TO-263 D <sup>2</sup> -PAK
QJxx16LH6	X	X	80 mA	Alternistor Triac	TO-220L
QJxx16RH6	X	X	80 mA	Alternistor Triac	TO-220R
QJxx16NH6	X	X	80 mA	Alternistor Triac	TO-263 D <sup>2</sup> -PAK

### Packing Options

Part Number	Marking	Weight	Packing Mode	Base Quantity
QJxx16L/RHyTP	QJxx16L/RHy	2.2 g	Tube Pack	500 (50 per tube)
QJxx16NHyTP	QJxx16NHy	1.6 g	Tube Pack	500 (50 per tube)
QJxx16NHyRP	QJxx16NHy	1.6 g	Embossed Carrier	500

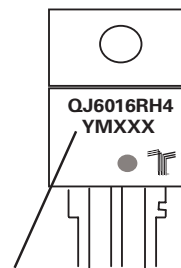
xx = voltage/10; y = Sensitivity

### Part Numbering System



### Part Marking System

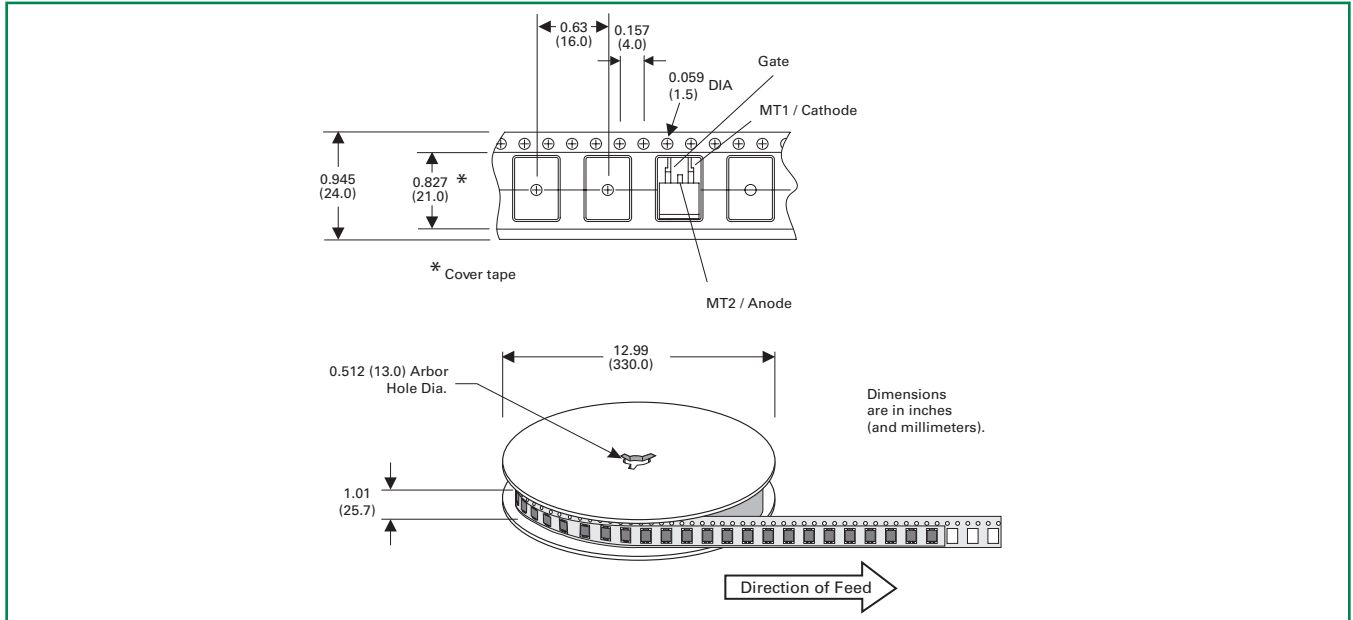
TO-220 AB - (L and R Package)  
TO-263 AB - (N Package)



Date Code Marking  
Y: Year Code  
M: Month Code  
XXX: Lot Trace Code

**TO-263 Embossed Carrier Reel Pack (RP)**

**Meets all EIA-481-2 Standards**



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